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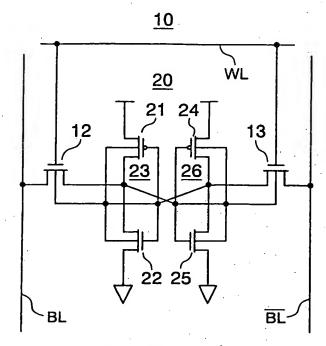
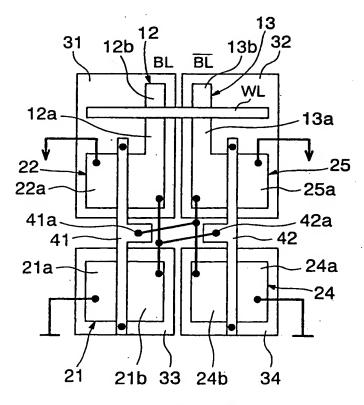


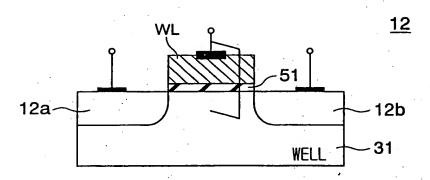
FIG.



F I G. 2

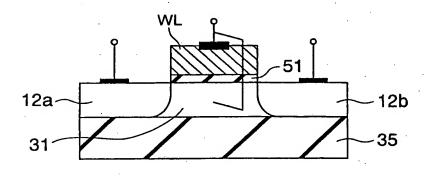
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USE OF ORDINARY SEMICONDUCTOR SUBSTRATE

FIG. 3A



USE OF SOI SUBSTRATE

FIG. 3B

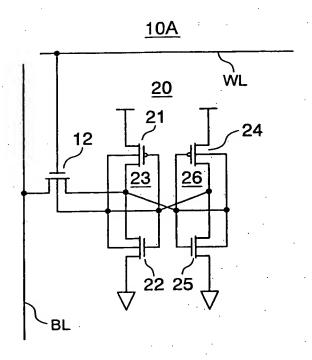


FIG. 4

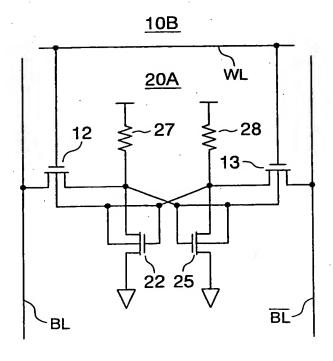


FIG. 5



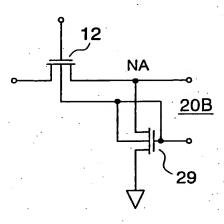
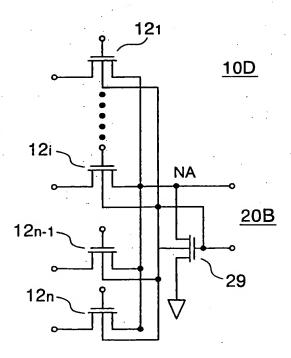
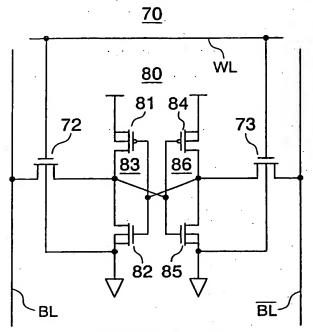


FIG. 6

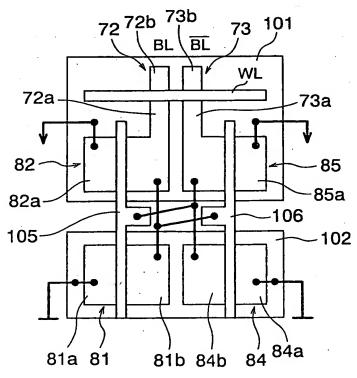


F1G. 7

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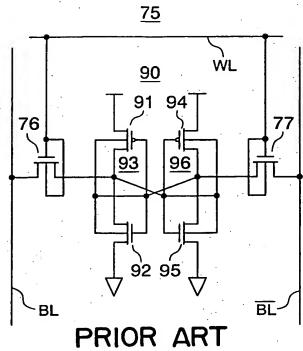


PRIOR ART FIG. 8

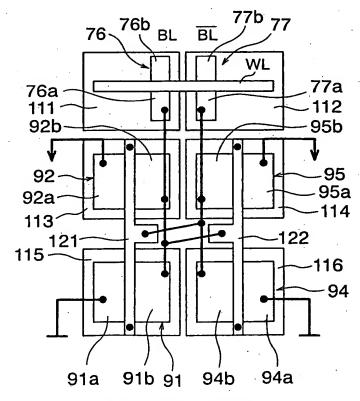


PRIOR ART FIG. 9

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PRIOR ART FIG. 10



PRIOR ART